TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOS III)

TPCF8102

Notebook PC Applications Portable Equipment Applications

- Low drain-source ON resistance: RDS (ON) = 24 m Ω (typ.)
- High forward transfer admittance: $|Y_{fs}| = 14 \text{ S (typ.)}$
- Low leakage current: $IDSS = -10 \mu A (max) (VDS = -20 V)$
- Enhancement mode: $V_{th} = -0.5 \text{ to } -1.2 \text{ V}$

 $(V_{DS} = -10 \text{ V}, I_{D} = -200 \text{ }\mu\text{A})$

Maximum Ratings (Ta = 25°C)

Characte	ristics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	-20	V	
Drain-gate voltage (R	_{GS} = 20 kΩ)	V _{DGR}	-20	V	
Gate-source voltage		V_{GSS}	±8	V	
Drain current	DC (Note 1)	I _D	-6	А	
Diam current	Pulsed (Note 1)	I _{DP}	-24		
Drain power dissipation	on $(t = 5 s)$ (Note 2a)	P_{D}	2.5	W	
Drain power dissipation	on (t = 5 s) (Note 2b)	P _D	0.7	W	
Single pulse avalanch	ne energy(Note 3)	E _{AS}	5.9	mJ	
Avalanche current		I _{AR}	-3	Α	
Repetitive avalanche	energy (Note 4)	E _{AR}	0.25	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature	range	T _{stg}	−55~150	°C	

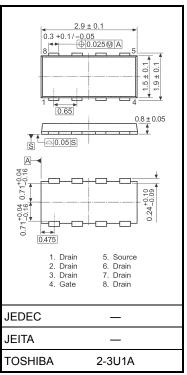
Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 5 s) (Note 2a)	R _{th (ch-a)}	50.0	°C/W
Thermal resistance, channel to ambient (t = 5 s) (Note 2b)	R _{th (ch-a)}	178.6	°C/W

Note 1, Note 2, Note 3, Note 4 and Note 5: See the next page.

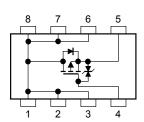
This transistor is an electrostatic-sensitive device. Please handle with caution.

Unit: mm



Weight: 0.011 g (typ.)

Circuit Configuration



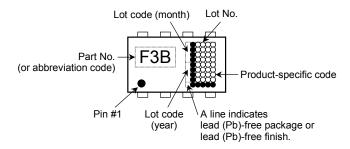
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cur	rent	I _{GSS}	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА	
Drain cut-off curr	ain cut-off current		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	-10	μА	
Drain-source breakdown voltage		V (BR) DSS	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-20	_	_	V	
		V (BR) DSX	$I_D = -10 \text{ mA}, V_{GS} = 8 \text{ V}$	-12	_	_	v	
Gate threshold ve	oltage	V _{th}	$V_{DS} = -10 \text{ V}, I_D = -200 \mu\text{A}$	-0.5	_	-1.2	٧	
		R _{DS (ON)}	$V_{GS} = -1.8 \text{ V}, I_D = -1.5 \text{ A}$	_	67	90		
Drain-source ON resistance		R _{DS} (ON)	$V_{GS} = -2.5 \text{ V}, I_D = -3.0 \text{ A}$	_	36	41	$m\Omega$	
		R _{DS} (ON)	$V_{GS} = -4.5 \text{ V}, I_D = -3.0 \text{ A}$	_	24	30		
Forward transfer admittance		Y _{fs}	$V_{DS} = -10 \text{ V}, I_D = -3.0 \text{ A}$	7	14	_	S	
Input capacitance		C _{iss}		_	1550	_	pF	
Reverse transfer capacitance		C _{rss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	215	_		
Output capacitance		Coss		_	265	_		
Switching time	Rise time	t _r	ACS -2 N D = -3.0 V V D = -3.0 V D	_	7	_		
	Turn-on time	t _{on}		_	13	_	- ns	
	Fall time	t _f	4.7 Ω 1.2 × × × × × × × × × × × × × × × × × × ×	_	21	_		
	Turn-off time	t _{off}	$V_{DD} \simeq -10 \text{ V}$ Duty \leq 1%, $t_W = 10 \mu\text{s}$	_	68	_		
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \simeq -16 \text{ V}, V_{GS} = -5 \text{ V},$	_	19	_		
Gate-source charge		Q _{gs}	$I_D = -6.0 \text{ A}$		14		nC	
Gate-drain ("miller") charge		Q _{gd}		_	5	_		

Source-Drain Ratings and Characteristics (Ta = 25°C)

Charact	Characteristics Symbol		Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)	I _{DRP}	_	_	_	-24	Α
Forward voltage (diode) V _{DSF}		V _{DSF}	$I_{DR} = -6.0 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	1.2	V

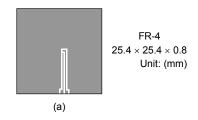
Marking (Note 5)

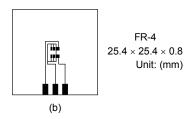


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)

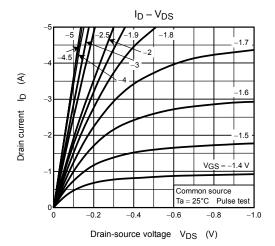


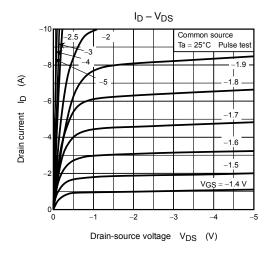


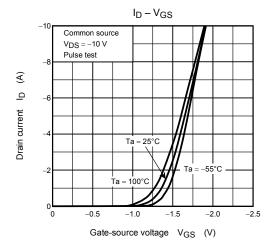
Note 3: $V_{DD} = -16~V$, $T_{ch} = 25^{\circ}C$ (initial), L = 0.5~mH, $R_G = 25~\Omega$, $I_{AR} = -3.0~A$

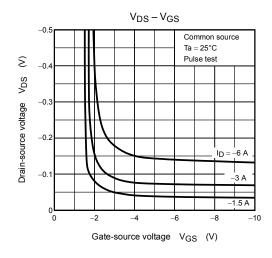
Note 4: Repetitive rating: pulse width limited by maximum channel temperature

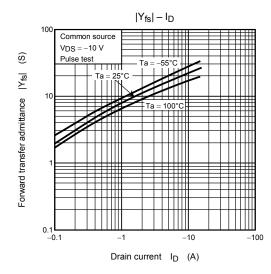
Note 5: A dot on the lower left of the marking indicates Pin 1.

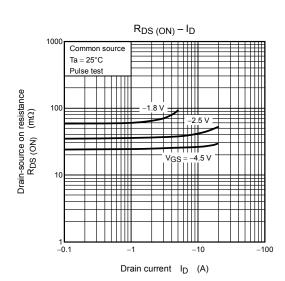


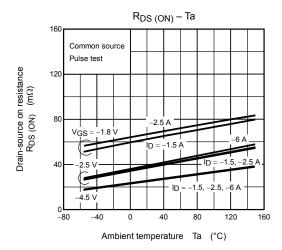


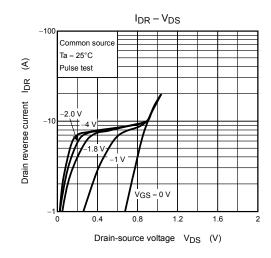


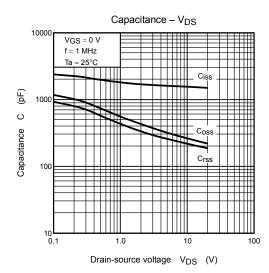


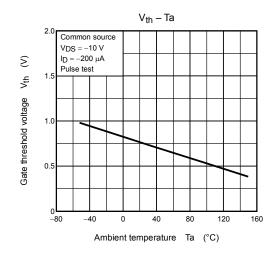


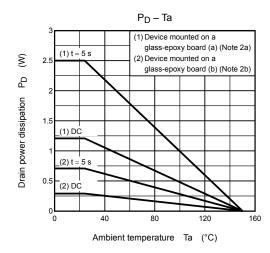


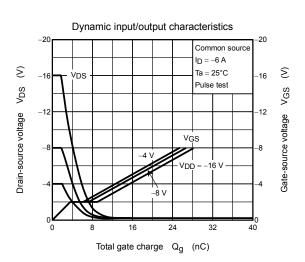




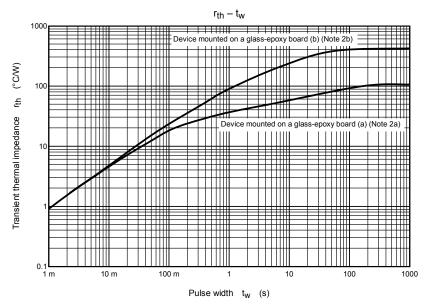


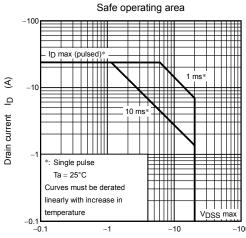






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Drain-source voltage V_{DS} (V)

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